

## IN THE SPECIFICATION

Please replace the title of the application on page 1, line 1, with the following new title:

### ~~IMAGE SENSOR MOUNTED BY MASS REFLOW~~ METHOD FOR FABRICATING AN IMAGE SENSOR MOUNTED BY MASS REFLOW

Please replace the paragraph beginning at page 10, line 7, with the following amended paragraph:

Fig. 13 is an exemplified view showing a second example of the planar construction of the supporting plate 400 and support 450. As shown therein, the supporting plate 400 or support 450 on which the semiconductor image pickup device 410 is loaded can be manufactured of Al or Al base alloy, Cu or Cu base alloy or Fe or Fe base alloy. By forming a water cooled tube 440 (not shown) on the regions contacting the substrate 420 where the semiconductor image pickup device 410 is formed, the heat generated in the thin film process can be spread more efficiently as compared to the first example of Fig. 6[[a]]. Thus, the surface temperature of the semiconductor image pickup device 410 can be kept at the range between a room temperature and 200°C.